

© Copyright SEK. Reproduction in any form without permission is prohibited.

**Halvledarkomponenter –  
Mikromekaniska komponenter –  
Del 25: Kiselbaserad tillverkning av MEMS –  
Mätning av drag-tryck- och skjuvningshållfasthet hos mikrobondade ytor**

*Semiconductor devices –  
Micro-electromechanical devices –  
Part 25: Silicon based MEMS fabrication technology –  
Measurement method of pull-press and shearing strength of micro bonding area*

Som svensk standard gäller europastandarden EN 62047-25:2016. Den svenska standarden innehåller den officiella engelska språkversionen av EN 62047-25:2016.

**Nationellt förord**

Europastandarden EN 62047-25:2016

består av:

- **europastandardens ikraftsättningsdokument**, utarbetat inom CENELEC
- **IEC 62047-25, First edition, 2016 - Semiconductor devices - Micro-electromechanical devices - Part 25: Silicon based MEMS fabrication technology - Measurement method of pull-press and shearing strength of micro bonding area**

utarbetad inom International Electrotechnical Commission, IEC.

---

ICS 31.080.99

## *Standarder underlättar utvecklingen och höjer elsäkerheten*

Det finns många fördelar med att ha gemensamma tekniska regler för bl a mätning, säkerhet och provning och för utförande, skötsel och dokumentation av elprodukter och elanläggningar.

Genom att utforma sådana standarder blir säkerhetsfordringar tydliga och utvecklingskostnaderna rimliga samtidigt som marknadens acceptans för produkten eller tjänsten ökar.

Många standarder inom elområdet beskriver tekniska lösningar och metoder som åstadkommer den elsäkerhet som föreskrivs av svenska myndigheter och av EU.

## *SEK är Sveriges röst i standardiseringsarbetet inom elområdet*

SEK Svensk Elstandard svarar för standardiseringen inom elområdet i Sverige och samordnar svensk medverkan i internationell och europeisk standardisering. SEK är en ideell organisation med frivilligt deltagande från svenska myndigheter, företag och organisationer som vill medverka till och påverka utformningen av tekniska regler inom elektrotekniken.

SEK samordnar svenska intressenters medverkan i SEKs tekniska kommittéer och stödjer svenska experters medverkan i internationella och europeiska projekt.

## *Stora delar av arbetet sker internationellt*

Utformningen av standarder sker i allt väsentligt i internationellt och europeiskt samarbete. SEK är svensk nationalkommitté av International Electrotechnical Commission (IEC) och Comité Européen de Normalisation Electrotechnique (CENELEC).

Standardiseringsarbetet inom SEK är organiserat i referensgrupper bestående av ett antal tekniska kommittéer som speglar hur arbetet inom IEC och CENELEC är organiserat.

Arbetet i de tekniska kommittéerna är öppet för alla svenska organisationer, företag, institutioner, myndigheter och statliga verk. Den årliga avgiften för deltagandet och intäkter från försäljning finansierar SEKs standardiseringsverksamhet och medlemsavgift till IEC och CENELEC.

## *Var med och påverka!*

Den som deltar i SEKs tekniska kommittéarbete har möjlighet att påverka framtida standarder och får tidig tillgång till information och dokumentation om utvecklingen inom sitt teknikområde. Arbetet och kontakterna med kollegor, kunder och konkurrenter kan gynnsamt påverka enskilda företags affärsutveckling och bidrar till deltagarnas egen kompetensutveckling.

Du som vill dra nytta av dessa möjligheter är välkommen att kontakta SEKs kansli för mer information.

## **SEK Svensk Elstandard**

Box 1284  
164 29 Kista  
Tel 08-444 14 00  
[www.elstandard.se](http://www.elstandard.se)

**EUROPEAN STANDARD**  
**NORME EUROPÉENNE**  
**EUROPÄISCHE NORM**

**EN 62047-25**

November 2016

ICS 31.080.99

English Version

**Semiconductor devices - Micro-electromechanical devices -  
Part 25: Silicon based MEMS fabrication technology -  
Measurement method of pull-press and shearing strength of  
micro bonding area  
(IEC 62047-25:2016)**

Dispositifs à semiconducteurs - Dispositifs  
microélectromécaniques - Partie 25: Technologie de  
fabrication de MEMS à base de silicium - Méthode de  
mesure de la résistance à la traction-compression et au  
cisaillement d'une micro zone de brasure  
(IEC 62047-25:2016)

Halbleiterbauelemente - Bauelemente der  
Mikrosystemtechnik - Teil 25: Siliziumbasierte MEMS-  
Herstellungstechnologie - Messverfahren zur Zug-Druck-  
und Scherfestigkeit gebondeter Flächen im  
Mikrometerbereich  
(IEC 62047-25:2016)

This European Standard was approved by CENELEC on 2016-10-03. CENELEC members are bound to comply with the CEN/CENELEC Internal Regulations which stipulate the conditions for giving this European Standard the status of a national standard without any alteration.

Up-to-date lists and bibliographical references concerning such national standards may be obtained on application to the CEN-CENELEC Management Centre or to any CENELEC member.

This European Standard exists in three official versions (English, French, German). A version in any other language made by translation under the responsibility of a CENELEC member into its own language and notified to the CEN-CENELEC Management Centre has the same status as the official versions.

CENELEC members are the national electrotechnical committees of Austria, Belgium, Bulgaria, Croatia, Cyprus, the Czech Republic, Denmark, Estonia, Finland, Former Yugoslav Republic of Macedonia, France, Germany, Greece, Hungary, Iceland, Ireland, Italy, Latvia, Lithuania, Luxembourg, Malta, the Netherlands, Norway, Poland, Portugal, Romania, Slovakia, Slovenia, Spain, Sweden, Switzerland, Turkey and the United Kingdom.



European Committee for Electrotechnical Standardization  
Comité Européen de Normalisation Electrotechnique  
Europäisches Komitee für Elektrotechnische Normung

**CEN-CENELEC Management Centre: Avenue Marnix 17, B-1000 Brussels**

## **European foreword**

The text of document 47F/249/FDIS, future edition 1 of IEC 62047-25, prepared by SC 47F "Microelectromechanical systems" of IEC/TC 47 "Semiconductor devices" was submitted to the IEC-CENELEC parallel vote and approved by CENELEC as EN 62047-25:2016.

The following dates are fixed:

- latest date by which the document has to be implemented at national level by publication of an identical national standard or by endorsement (dop) 2017-07-03
- latest date by which the national standards conflicting with the document have to be withdrawn (dow) 2019-10-03

Attention is drawn to the possibility that some of the elements of this document may be the subject of patent rights. CENELEC [and/or CEN] shall not be held responsible for identifying any or all such patent rights.

## **Endorsement notice**

The text of the International Standard IEC 62047-25:2016 was approved by CENELEC as a European Standard without any modification.

**Annex ZA**  
(normative)

**Normative references to international publications  
with their corresponding European publications**

The following documents, in whole or in part, are normatively referenced in this document and are indispensable for its application. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

NOTE 1 When an International Publication has been modified by common modifications, indicated by (mod), the relevant EN/HD applies.

NOTE 2 Up-to-date information on the latest versions of the European Standards listed in this annex is available here:  
[www.cenelec.eu](http://www.cenelec.eu)

<u>Publication</u>	<u>Year</u>	<u>Title</u>	<u>EN/HD</u>	<u>Year</u>
IEC 62047-1	-	Semiconductor devices - Micro-electromechanical devices - Part 1: Terms and definitions	EN 62047-1	-
ISO 10012	-	Measurement management systems - Requirements for measurement processes and measuring equipment	EN ISO 10012	-

## CONTENTS

FOREWORD.....	4
1 Scope.....	6
2 Normative references.....	6
3 Terms and definitions .....	6
4 Requirements .....	7
4.1 Testing structure design requirements .....	7
4.2 Testing structure fabrication requirements .....	9
4.3 Testing environment requirements.....	9
5 Testing method.....	9
5.1 General.....	9
5.2 Pull-press testing method .....	9
5.2.1 Imposing the loading force .....	9
5.2.2 Pull-press testing method operation process.....	9
5.2.3 Pull-press testing method result process.....	10
5.3 Shearing testing method.....	10
5.3.1 Shearing testing method operation process .....	10
5.3.2 Shearing testing method result process .....	12
Annex A (informative) Dimensions for testing structure and tensile/compressive strength.....	13
A.1 Dimensions for testing structure .....	13
A.2 Tensile strength and compressive strength .....	13
Annex B (informative) Pull-press testing method example .....	21
B.1 Dimensions for testing structure .....	21
B.2 Tensile strength and compressive strength .....	21
Figure 1 – Pull-press testing structure .....	7
Figure 2 – Shearing testing structure.....	8
Figure 3 – Pull-press testing method operation process .....	10
Figure 4 – Shearing testing method operation process.....	11
Table 1 – Dimensions for shearing testing structure.....	12
Table A.1 – Dimensions for testing structure.....	13
Table A.2 – Tensile strength and compressive strength (bonding area: 10 µm × 10 µm).....	13
Table A.3 – Tensile strength and compressive strength (bonding area: 20 µm × 20 µm).....	14
Table A.4 – Tensile strength and compressive strength (bonding area: 30 µm × 30 µm).....	14
Table A.5 – Tensile strength and compressive strength (bonding area: 40 µm × 40 µm).....	15
Table A.6 – Tensile strength and compressive strength (bonding area: 50 µm × 50 µm).....	15
Table A.7 – Tensile strength and compressive strength (bonding area: 60 µm × 60 µm).....	15
Table A.8 – Tensile strength and compressive strength (bonding area: 70 µm × 70 µm).....	16
Table A.9 – Tensile strength and compressive strength (bonding area: 80 µm × 80 µm).....	16
Table A.10 – Tensile strength and compressive strength (bonding area: 90 µm × 90 µm).....	17
Table A.11 – Tensile strength and compressive strength (bonding area: 100 µm × 100 µm).....	17

Table A.12 – Tensile strength and compressive strength (bonding area: 110 µm × 110 µm).....	18
Table A.13 – Tensile strength and compressive strength (bonding area: 120 µm × 120 µm).....	18
Table A.14 – Tensile strength and compressive strength (bonding area: 130 µm × 130 µm).....	19
Table A.15 – Tensile strength and compressive strength (bonding area: 140 µm × 140 µm).....	19
Table A.16 – Tensile strength and compressive strength (bonding area: 150 µm × 150 µm).....	20
Table B.1 – Dimensions for testing structure.....	21
Table B.2 – Tensile strength and compressive strength (bonding area: 110 µm × 110 µm).....	21

## INTERNATIONAL ELECTROTECHNICAL COMMISSION

---

**SEMICONDUCTOR DEVICES –  
MICRO-ELECTROMECHANICAL DEVICES –****Part 25: Silicon based MEMS fabrication technology – Measurement  
method of pull-press and shearing strength of micro bonding area****FOREWORD**

- 1) The International Electrotechnical Commission (IEC) is a worldwide organization for standardization comprising all national electrotechnical committees (IEC National Committees). The object of IEC is to promote international co-operation on all questions concerning standardization in the electrical and electronic fields. To this end and in addition to other activities, IEC publishes International Standards, Technical Specifications, Technical Reports, Publicly Available Specifications (PAS) and Guides (hereafter referred to as "IEC Publication(s)"). Their preparation is entrusted to technical committees; any IEC National Committee interested in the subject dealt with may participate in this preparatory work. International, governmental and non-governmental organizations liaising with the IEC also participate in this preparation. IEC collaborates closely with the International Organization for Standardization (ISO) in accordance with conditions determined by agreement between the two organizations.
- 2) The formal decisions or agreements of IEC on technical matters express, as nearly as possible, an international consensus of opinion on the relevant subjects since each technical committee has representation from all interested IEC National Committees.
- 3) IEC Publications have the form of recommendations for international use and are accepted by IEC National Committees in that sense. While all reasonable efforts are made to ensure that the technical content of IEC Publications is accurate, IEC cannot be held responsible for the way in which they are used or for any misinterpretation by any end user.
- 4) In order to promote international uniformity, IEC National Committees undertake to apply IEC Publications transparently to the maximum extent possible in their national and regional publications. Any divergence between any IEC Publication and the corresponding national or regional publication shall be clearly indicated in the latter.
- 5) IEC itself does not provide any attestation of conformity. Independent certification bodies provide conformity assessment services and, in some areas, access to IEC marks of conformity. IEC is not responsible for any services carried out by independent certification bodies.
- 6) All users should ensure that they have the latest edition of this publication.
- 7) No liability shall attach to IEC or its directors, employees, servants or agents including individual experts and members of its technical committees and IEC National Committees for any personal injury, property damage or other damage of any nature whatsoever, whether direct or indirect, or for costs (including legal fees) and expenses arising out of the publication, use of, or reliance upon, this IEC Publication or any other IEC Publications.
- 8) Attention is drawn to the Normative references cited in this publication. Use of the referenced publications is indispensable for the correct application of this publication.
- 9) Attention is drawn to the possibility that some of the elements of this IEC Publication may be the subject of patent rights. IEC shall not be held responsible for identifying any or all such patent rights.

International Standard IEC 62047-25 has been prepared by subcommittee 47F: Micro-electromechanical systems, of IEC technical committee 47: Semiconductor devices.

The text of this standard is based on the following documents:

FDIS	Report on voting
47F/249/FDIS	47F/252/RVD

Full information on the voting for the approval of this standard can be found in the report on voting indicated in the above table.

This publication has been drafted in accordance with the ISO/IEC Directives, Part 2.

The committee has decided that the contents of this publication will remain unchanged until the stability date indicated on the IEC website under "http://webstore.iec.ch" in the data related to the specific publication. At this date, the publication will be

- reconfirmed,
- withdrawn,
- replaced by a revised edition, or
- amended.

**IMPORTANT – The 'colour inside' logo on the cover page of this publication indicates that it contains colours which are considered to be useful for the correct understanding of its contents. Users should therefore print this document using a colour printer.**

## SEMICONDUCTOR DEVICES – MICRO-ELECTROMECHANICAL DEVICES –

### **Part 25: Silicon based MEMS fabrication technology – Measurement method of pull-press and shearing strength of micro bonding area**

#### **1 Scope**

This part of IEC 62047 specifies the in-situ testing method to measure the bonding strength of micro bonding area which is fabricated by micromachining technologies used in silicon-based micro-electromechanical system (MEMS).

This document is applicable to the in-situ pull-press and shearing strength measurement of the micro bonding area fabricated by microelectronic technology process and other micromachining technology.

Micro anchor, fixed on the substrate through the micro bonding area, provides mechanical support of the movable sensing/actuating functional components in MEMS devices. With the devices scaling, the bonding strength degradation, induced by defects, contaminations and thermal mismatch stress on bonding surface, becomes severer. This standard specifies an in-situ testing method of the pull-press and shearing strength based on a patterned technique. This document does not need intricate instruments (such as scanning probe microscopy and nanoindenter) and to prepare the test specimen specially.

Since the testing structure in this standard can be implanted in device fabrication as a standard detection pattern, this document can provide a bridge, by which the fabrication foundry can give some quantitative reference for the designer.

#### **2 Normative references**

The following documents are referred to in the text in such a way that some or all of their content constitutes requirements of this document. For dated references, only the edition cited applies. For undated references, the latest edition of the referenced document (including any amendments) applies.

IEC 62047-1, *Semiconductor devices – Micro-electromechanical devices – Part 1: Terms and definitions*

ISO 10012, *Measurement management systems – Requirements for measurement processes and measuring equipment*